Low-Voltage CMOS Octal D-Type Flip-Flop

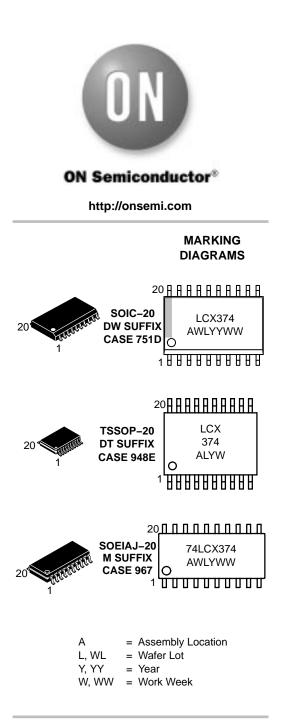
With 5 V–Tolerant Inputs and Outputs (3–State, Non–Inverting)

The MC74LCX374 is a high performance, non-inverting octal D-type flip-flop operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX374 inputs to be safely driven from 5 V devices.

The MC74LCX374 consists of 8 edge-triggered flip-flops with individual D-type inputs and 3-state true outputs. The buffered clock and buffered Output Enable (\overline{OE}) are common to all flip-flops. The eight flip-flops will store the state of individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CP) transition. With the \overline{OE} LOW, the contents of the eight flip-flops are available at the outputs. When the \overline{OE} is HIGH, the outputs go to the high impedance state. The \overline{OE} input level does not affect the operation of the flip-flops.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0$ V
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- Pb–Free Packages are Available*



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

© Semiconductor Components Industries, LLC, 2005 January, 2005 – Rev. 7

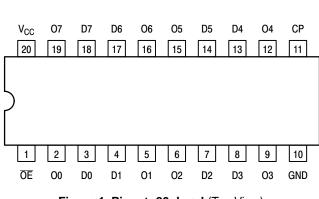
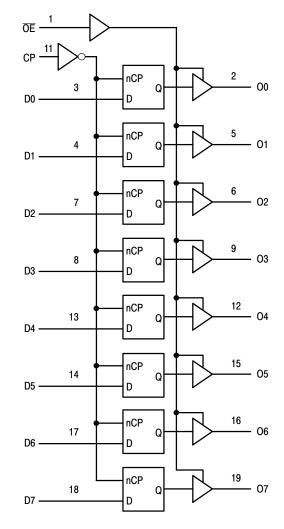


Figure 1. Pinout: 20-Lead (Top View)

PIN NAMES

Pins	Function
ŌĒ	Output Enable Input
CP	Clock Pulse Input
D0-D7	Data Inputs
00–07	3-State Outputs





TRUTH TABLE

	INPUTS		OUTPUTS	
ŌĒ	СР	Dn	On	OPERATING MODE
L	$\stackrel{\uparrow}{\leftarrow}$	l h	L H	Load and Read Register
L	1	Х	NC	Hold and Read Register
Н	1	х	Z	Hold and Disable Outputs
H H	$\uparrow \\ \uparrow$	l h	Z Z	Load Internal Register and Disable Outputs

Н High Voltage Level =

h High Voltage Level One Setup Time Prior to the Low-to-High Clock Transition =

Low Voltage Level L =

Low Voltage Level One Setup Time Prior to the Low-to-High Clock Transition 1 =

NC = No Change, State Prior to Low-to-High Clock Transition

- = High or Low Voltage Level and Transitions are Acceptable Х
- = High Impedance State

Z ↑ = Low-to-High Transition

≄ Not a Low-to-High Transition; For I_{CC} Reasons, DO NOT FLOAT Inputs =

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_I \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	$V_{O} > V_{CC}$	mA
lo	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage Da	Operating ta Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage (HI	GH or LOW State) (3–State)	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0 V - 3.6 V	1			-24	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$				24	mA
I _{OH}	HIGH Level Output Current, $V_{CC} = 2.7 V - 3.0 V_{CC}$	/			-12	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 2.7 V - 3.0 V$				12	mA
T _A	Operating Free–Air Temperature		-40		+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate, VIN from 0.8	/ to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX374DWR2	SOIC-20	1000 Tape & Reel
MC74LCX374DR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX374DTR2	TSSOP-20*	2000 Tape & Reel
MC74LCX374MEL	SOEIAJ-20	2000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
VIH	HIGH Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}$	2.0		V
V _{IL}	LOW Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}$		0.8	V
V _{OH}	HIGH Level Output Voltage	2.7 V \leq V_{CC} \leq 3.6 V; I_{OH} = –100 μA	V _{CC} – 0.2		V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		

2. These values of V_I are used to test DC electrical characteristics only.

DC ELECTRICAL CHARACTERISTICS (Continued)

			$T_A = -40^{\circ}$	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{OL}	LOW Level Output Voltage	$2.7~\text{V} \leq \text{V}_{CC} \leq 3.6~\text{V};~\text{I}_{OL}$ = 100 μA		0.2	V
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
l _l	Input Leakage Current	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}; \text{ 0 V} \leq \text{V}_{I} \leq 5.5 \text{ V}$		±5.0	μA
I _{OZ}	3–State Output Current	$\begin{array}{c} 2.7 \leq V_{CC} \leq 3.6 \text{ V}; \ 0 \text{ V} \leq V_O \leq 5.5 \text{ V}; \\ \text{V}_I = \text{V}_{IH} \text{ or V}_{IL} \end{array}$		±5.0	μΑ
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 V; V_{I} \text{ or } V_{O} = 5.5 V$		10	μΑ
I _{CC}	Quiescent Supply Current	$2.7 \leq V_{CC} \leq 3.6$ V; V_I = GND or V_{CC}		10	μA
		$2.7 \leq V_{CC} \leq 3.6$ V; $3.6 \leq V_{I}$ or $V_{O} \leq 5.5$ V		±10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.7 \le V_{CC} \le 3.6$ V; $V_{IH} = V_{CC} - 0.6$ V		500	μA

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω)

				Lin	nits		
				T _A = −40°C	C to +85°C		
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	: 2.7 V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
f _{max}	Clock Pulse Frequency	1	150				MHz
t _{PLH} t _{PHL}	Propagation Delay CP to O _n	1	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t _{PZH} t _{PZL}	Output Enable Time to HIGH and LOW Levels	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t _{PHZ} t _{PLZ}	Output Disable Time from HIGH and LOW Levels	2	1.5 1.5	7.5 7.5	1.5 1.5	8.5 8.5	ns
t _s	Setup TIme, HIGH or LOW D _n to CP	1	2.5		2.5		ns
t _h	Hold Time, HIGH or LOW D _n to CP	1	1.5		1.5		ns
tw	CP Pulse Width, HIGH or LOW	3	3.3		3.3		ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0			ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

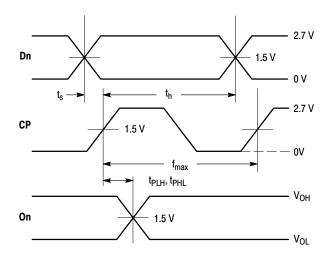
DYNAMIC SWITCHING CHARACTERISTICS

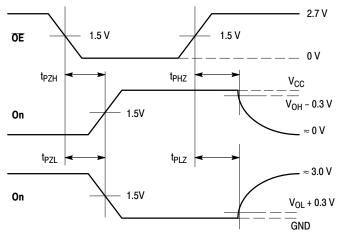
			T,	₄ = +25°	С	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	V_{CC} = 3.3 V, C_{L} = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V		0.8		V

4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

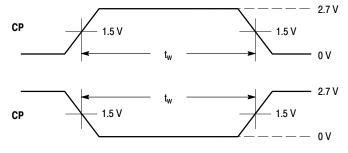
Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF





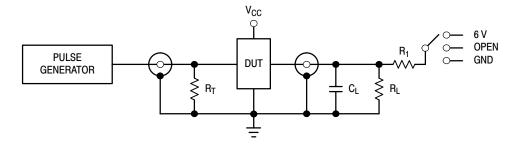
WAVEFORM 1 - PROPAGATION DELAYS, SETUP AND HOLD TIMES t_{R} = t_{F} = 2.5 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES $t_{R} = t_{F} = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_{W} = 500$ ns



WAVEFORM 3 - PULSE WIDTH $t_{R} = t_{F} = 2.5$ ns (or fast as required) from 10% to 90%; Output requirements: V_{OL} \leq 0.8 V, V_{OH} \geq 2.0 V





TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V
Open Collector/Drain t_{PLH} and t_{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

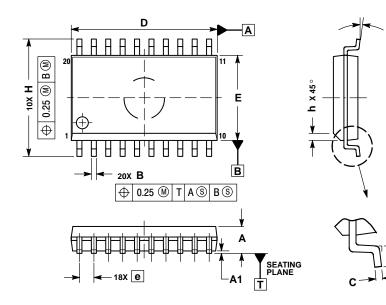
 C_L = 50 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**

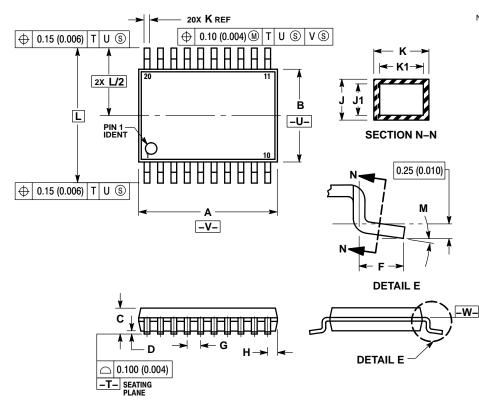


NOTES:

- 1. 2.
- DIMENSIONS ARE IN MILLIMETERS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD 3. PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B 5. DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

TSSOP-20 DT SUFFIX CASE 948E-02 ISSUE B



NOTES:

DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SUDE

SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER

SIDE. 5. DIMENSION K DOES NOT INCLUDE 5. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 5. TERMINAL NUMBERS ARE SHOWN

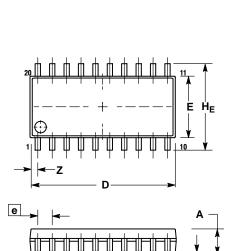
6.

FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-. 7

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
Μ	0°	8°	0 °	8°

PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 ISSUE O



– b

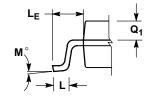
0.13 (0.005) 🕅

 \oplus

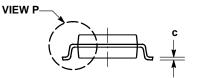
A₁

0.10 (0.004)

 \Box



DETAIL P



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PFR SIDE.
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
A		2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.18	0.27	0.007	0.011	
D	12.35	12.80	0.486	0.504	
Е	5.10	5.45	0.201	0.215	
е	1.27 BSC		0.050 BSC		
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
М	0 °	10 °	0 °	10 °	
Q ₁	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters visual in fire, or forany other application in which the failure of the SCILLC product source as components in systems intended for surgical implant into the body, or other applications in which the SCILLC product cate a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850 ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.